

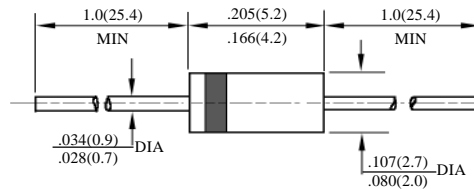
BA157G – BA159G

 快速玻钝二极管
 FAST GPP DIODES

型号 TYPE	最大反向 峰值电压 Maximum Peak Reverse Voltage	最大平均正向电流 Maximum Average Rectified Current @ Half-Wave Resistive Load 60Hz		最大正向浪涌电流 Maximum Forward Peak Surge Current @ 8.3ms Superimposed	最大反向漏电电流 Maximum Reverse Current @ PRV @ T _A =25°C	最大正向电压 Maximum Forward Voltage @ T _A =25°C		最大反向 恢复时间 Maximum Reverse Recovery Time	外型尺寸 Package Dimensions
	PRV	I _O @ T _L		I _{FM} (Surge)	I _R	I _{FM}	V _{FM}	T _{rr}	
	V _{PK}	A _{AV}	°C	A _{PK}	μA _{dc}	A _{PK}	V _{PK}	ns	
BA157G	400	1.0	55	20	5.0	1.0	1.3	150	DO-41
BA158G	600							250	
BA159DG	800							500	
BA159G	1000							500	

T_{rr}测试条件: I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A

T_{rr} Test Conditions: I_F = 0.5A, I_R = 1.0A, I_{RR} = 0.25A



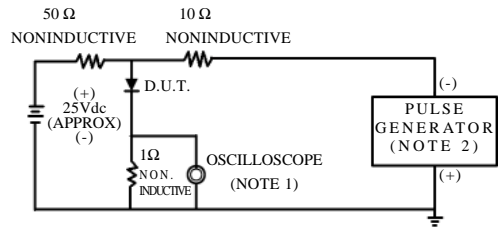
DO – 41

BA157G-BA159G

快速 GPP 二极管额定值与特性曲线

RATING & CHARACTERISTIC CURVES OF FAST GPP DIODE

FIG.1 – TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTIC



NOTES: 1. Rise Time=7ns max.
Input Impedance=1megohm.22pF.
2. Rise Time=10ns max.
Source Impedance=50 ohms.

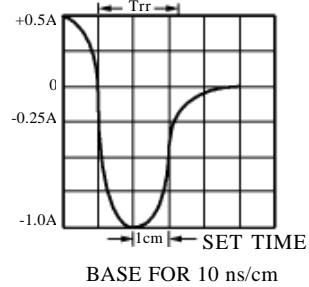


FIG. 2 – TYPICAL FORWARD CURRENT DERATING CURVE

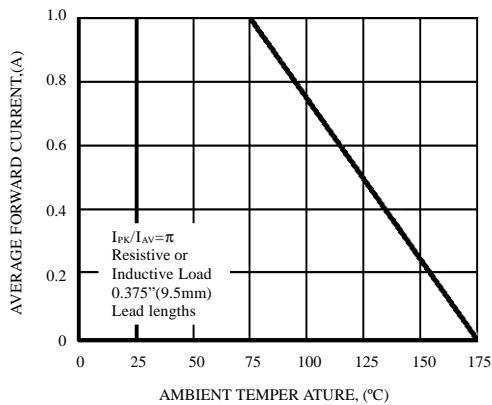


FIG.3 – TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

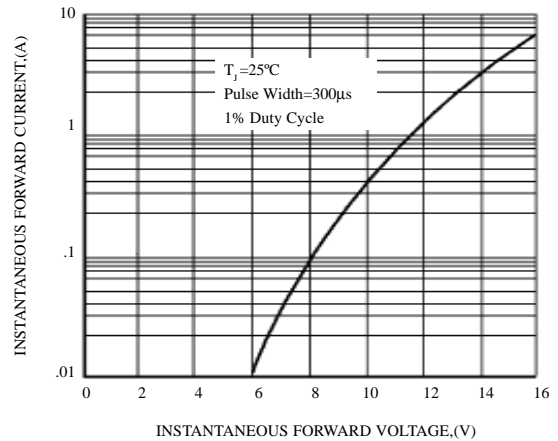


FIG.4 – TYPICAL JUNCTION CAPACITANCE

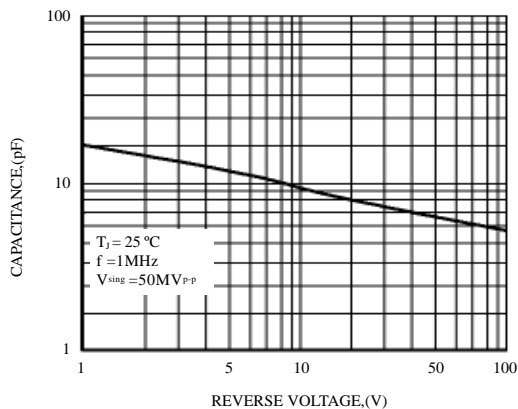


FIG.5 – MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

